

N-channel 80 V, 25 mΩ standard level MOSFET in LFPAK56 8 May 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	39	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	95	W
Static charact	eristics				- 1	_	
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11		-	16.7	25	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 10 A; V _{DS} = 64 V; T _j = 25 °C; <u>Fig. 13; Fig. 14</u>		-	8.2	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UFT4
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK7Y25-80E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7Y25-80E	72580E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

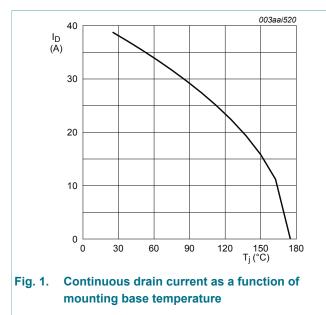
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	39	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	27.5	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4	-	156	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	95	W
T _{stg}	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-dra	in diode		1			
I _S	source current	T _{mb} = 25 °C		-	39	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	156	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ I_D = 39 \text{ A}; V_{sup} \le 80 \text{ V}; \text{ R}_{GS} = 50 \Omega; V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}; Fig. 3 $	[1][2]	-	43.6	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^\circ\text{C}.$

[2] Refer to application note AN10273 for further information.



 $V_{GS} \ge 10V$

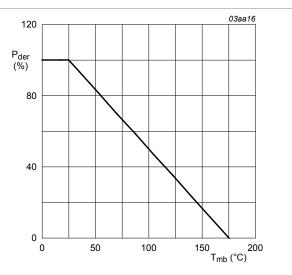
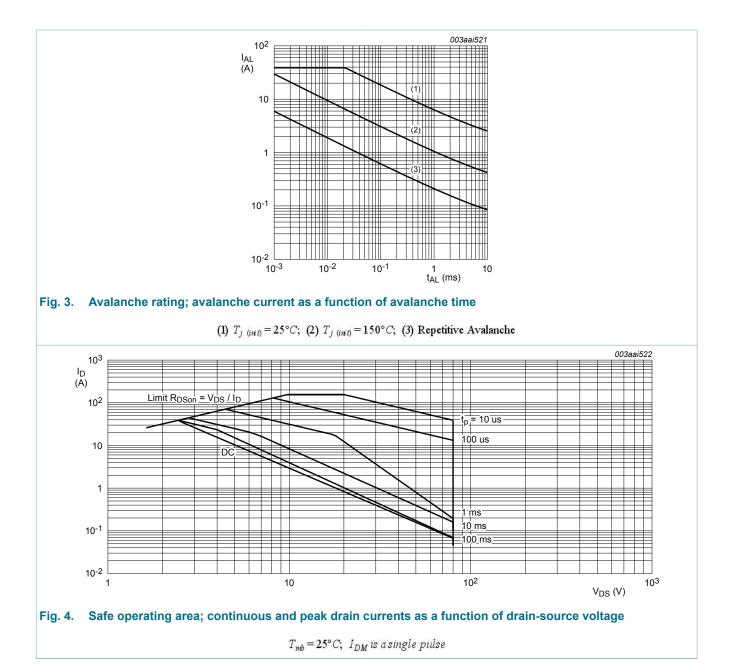


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

BUK7Y25-80E

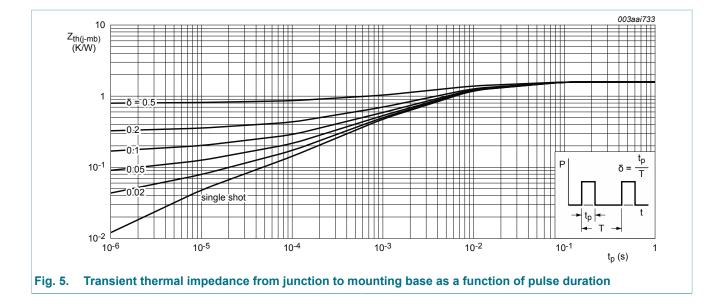
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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.58	K/W

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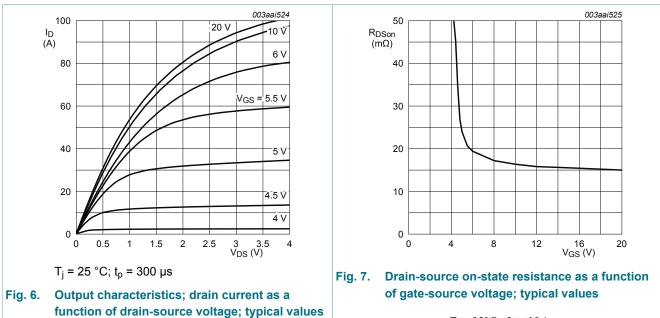
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics	· · ·	I				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V	
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V	
V _{GS(th)} gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V		
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V	
I _{DSS}	DSS drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA	
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA	
I _{GSS} gate leakage of	I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11	-	16.7	25	mΩ	
		V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	62.75	mΩ	
Dynamic ch	naracteristics	· · ·	'				
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 64 V; V _{GS} = 10 V;	-	25.9	-	nC	
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	5.9	-	nC	
Q _{GD}	gate-drain charge	1	-	8.2	-	nC	

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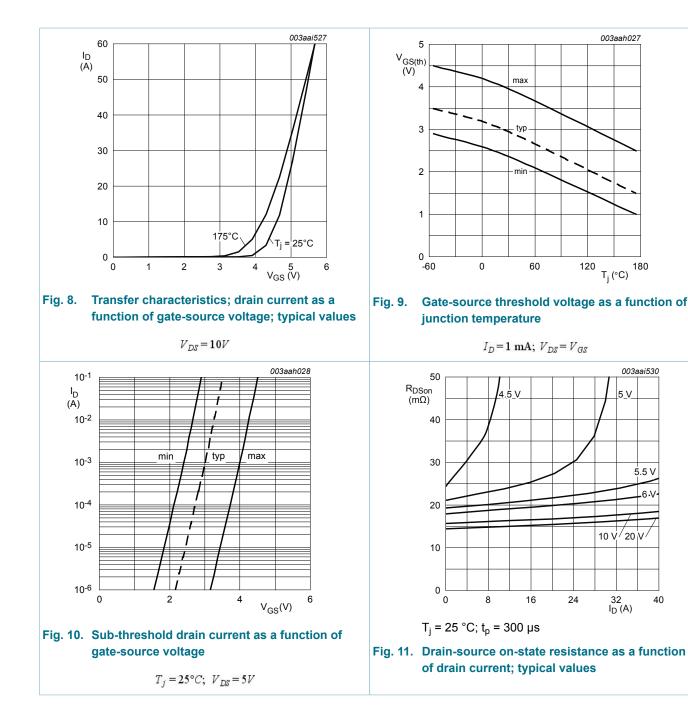
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>		-	1364	1800	pF
C _{oss}	output capacitance			-	150	180	pF
C _{rss}	reverse transfer capacitance			-	92	127	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 60 \text{ V}; \text{ R}_{L} = 5 \Omega; \text{ V}_{GS} = 10 \text{ V};$ $\text{R}_{G(ext)} = 5 \Omega; \text{ T}_{j} = 25 ^{\circ}\text{C}$		-	6.9	-	ns
t _r	rise time			-	9.2	-	ns
t _{d(off)}	turn-off delay time			-	17.5	-	ns
t _f	fall time			-	10.5	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I_{S} = 10 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A; } dI_{S}/dt = -100 \text{ A}/\mu\text{s; } V_{GS} = 0 \text{ V;}$ $V_{DS} = 25 \text{ V; } T_{j} = 25 \text{ °C}$		-	25.4	-	ns
Q _r	recovered charge			-	30.7	-	nC



 $T_j = 25^{\circ}C; I_D = 10A$

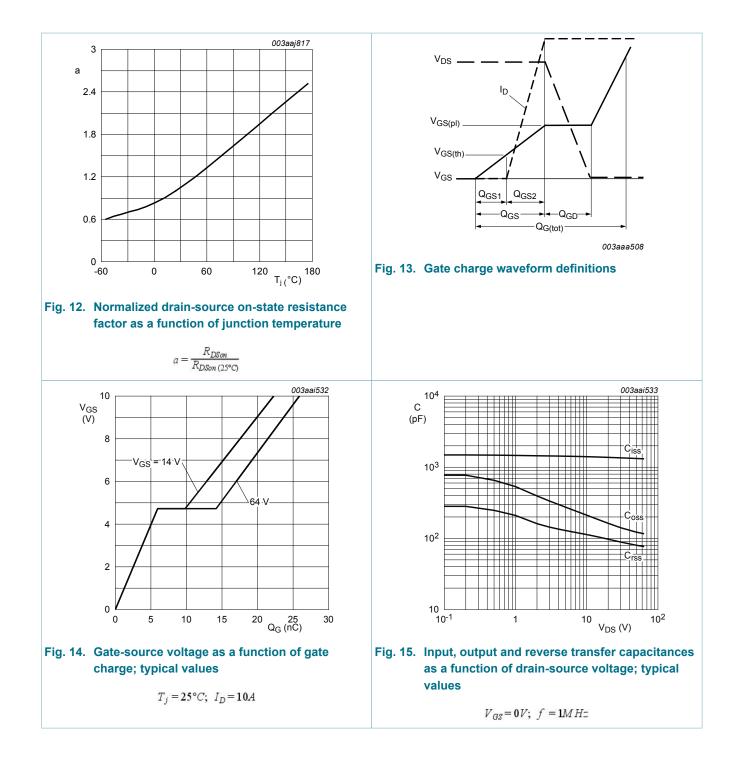
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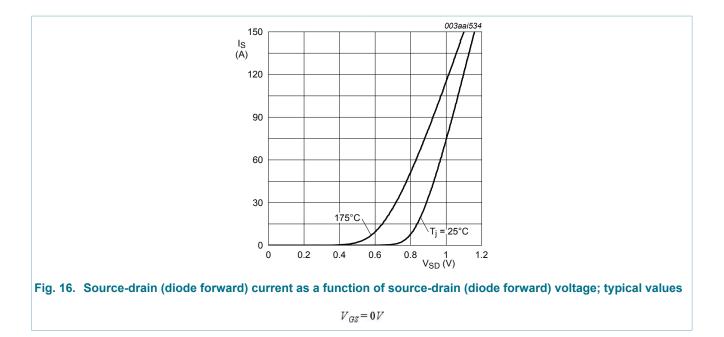
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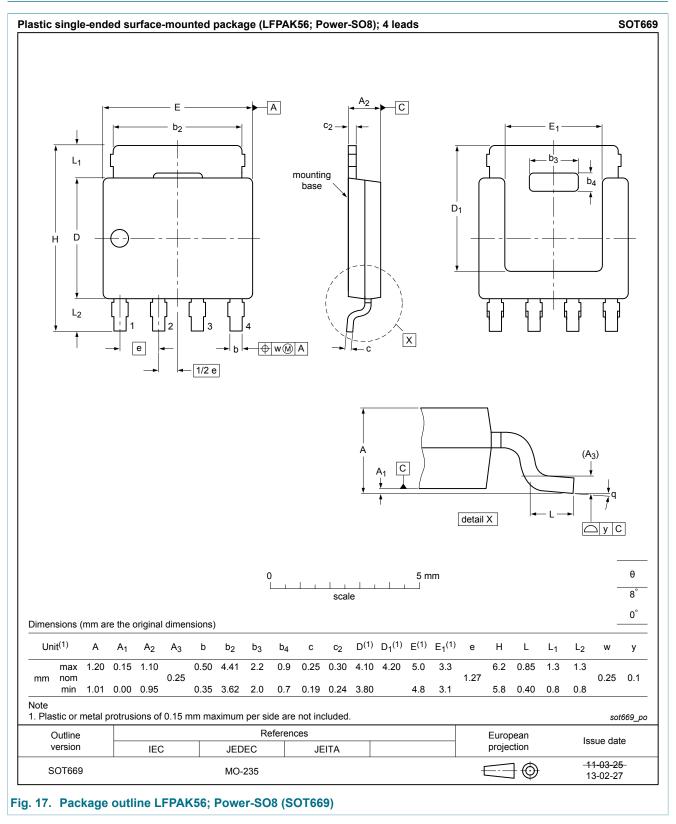
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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